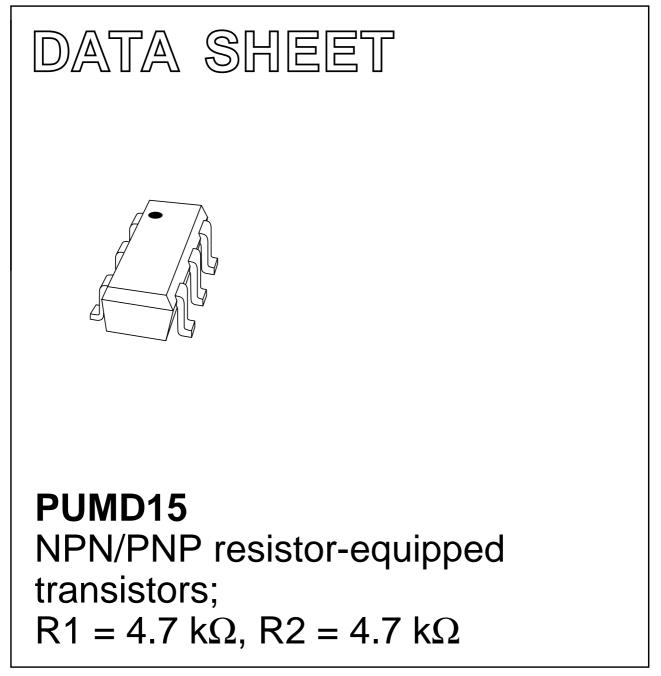
## DISCRETE SEMICONDUCTORS



Product specification

2004 Feb 04



## NPN/PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$

### PUMD15

#### FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

#### APPLICATIONS

- Low current peripheral driver
- Replacement of general purpose transistors in digital applications
- Control of IC inputs.

#### DESCRIPTION

NPN/PNP resistor-equipped transistors (see "Simplified outline, symbol and pinning" for package details).

#### **PRODUCT OVERVIEW**

TYPE	PACKAGE		MARKING CODE	PNP/PNP	NPN/NPN	
NUMBER	PHILIPS	EIAJ	MARKINGCODE	COMPLEMENT	COMPLEMENT	
PUMD15	SOT363	SC-88	D0* <sup>(1)</sup>	PUMB15	PUMH15	

#### Note

- 1. \* = p: Made in Hong Kong.
  - \* = t: Made in Malaysia.
    - \* = W: Made in China.

#### SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL		PINNING		
ITFE NOWBER	SIMPLIFIED OUTLINE AND STMBOL			DESCRIPTION	
PUMD15		6 5 4	1	emitter TR1	
			2	base TR1	
			3	collector TR2	
			4	emitter TR2	
			5	base TR2	
			6	collector TR1	
		1 2 3			
	Top view	MAM468			

#### QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	-	50	V
lo	output current (DC)	-	100	mA
TR1	NPN	-	_	-
TR2	PNP	-	_	-
R1	bias resistor	4.7	_	kΩ
R2	bias resistor	4.7	_	kΩ

# NPN/PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$

### PUMD15

#### **ORDERING INFORMATION**

	PACKAGE				
	NAME	DESCRIPTION	VERSION		
PUMD15	—	plastic surface mounted package; 6 leads	SOT363		

#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT	
Per transistor; for the PNP transistor with negative polarity						
V <sub>CBO</sub>	collector-base voltage	open emitter	-	50	V	
V <sub>CEO</sub>	collector-emitter voltage	open base	-	50	V	
V <sub>EBO</sub>	emitter-base voltage	open collector	-	10	V	
VI	input voltage TR1					
	positive		-	+30	V	
	negative		-	-10	V	
VI	input voltage TR2					
	positive		-	+10	V	
	negative		-	-30	V	
lo	output current (DC)		-	100	mA	
I <sub>CM</sub>	peak collector current		-	100	mA	
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C;$ note 1	-	200	mW	
T <sub>stg</sub>	storage temperature		-65	+150	°C	
Tj	junction temperature		-	150	°C	
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C	
Per device	•					
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C;$ note 1	_	300	mW	

#### Note

1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per transist	or			
R <sub>th j-a</sub>	thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^{\circ}C$ ; note 1	625	K/W
Per device				
R <sub>th j-a</sub>	thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^{\circ}C$ ; note 1	416	K/W

Note

1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.

## NPN/PNP resistor-equipped transistors; R1 = 4.7 k\Omega, R2 = 4.7 k\Omega

## PUMD15

#### CHARACTERISTICS

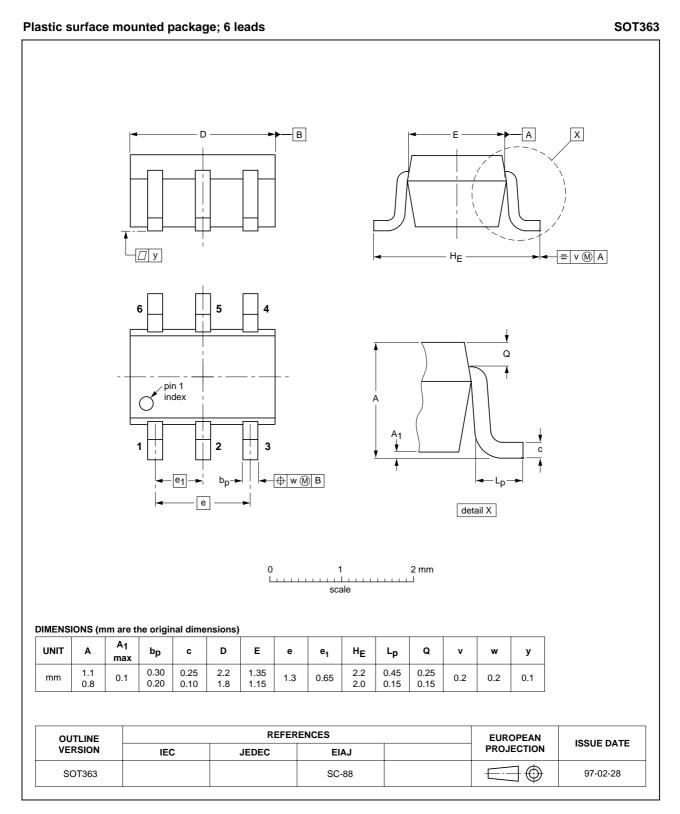
 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per transis	Per transistor; for the PNP transistor with negative polarity					
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 50 \text{ V}; \text{ I}_{E} = 0$	_	-	100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	$V_{CE} = 30 \text{ V}; \text{ I}_{B} = 0$	-	-	1	μA
		$V_{CE} = 30 \text{ V}; \text{ I}_{B} = 0; \text{ T}_{j} = 150 ^{\circ}\text{C}$	-	-	50	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 V; I_{C} = 0$	-	-	0.9	mA
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}$	30	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 0.5 mA	-	-	150	mV
V <sub>i(off)</sub>	input-off voltage	$I_{C} = 100 \ \mu\text{A}; \ V_{CE} = 5 \ V$	-	1.1	0.5	V
V <sub>i(on)</sub>	input-on voltage	I <sub>C</sub> = 20 mA; V <sub>CE</sub> = 0.3 V	2.5	1.9	_	V
R1	input resistor		3.3	4.7	6.1	kΩ
R2 R1	resistor ratio		0.8	1	1.2	
C <sub>c</sub>	collector capacitance	I <sub>E</sub> = i <sub>e</sub> = 0; V <sub>CB</sub> = 10 V; f = 1 MHz				
	TR1 (NPN)		-	-	2.5	pF
	TR2 (PNP)		-	-	3	pF

PUMD15

## NPN/PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$

#### PACKAGE OUTLINES



### NPN/PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$

PUMD15

#### DATA SHEET STATUS

LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)(3)</sup>	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
11	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

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- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

#### DEFINITIONS

**Short-form specification** — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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